Abstracts

MEMS single-pole double-throw (SPDT) X and K-band switching circuits

S.P. Pacheco, D. Peroulis and L.P.B. Katehi. "MEMS single-pole double-throw (SPDT) X and K-band switching circuits." 2001 MTT-S International Microwave Symposium Digest 01.1 (2001 Vol. I [MWSYM]): 321-324 vol.1.

Single-pole double-throw (SPDT) X and K-band circuit designs incorporating low-loss microelectromechanical shunt capacitive switches are reported. The switches incorporate highly inductive connecting beams which aid in further increasing the isolation at the desired operational RF frequency. Measurements show an isolation of better than 40 dB at both 7 and 20 GHz. Insertion loss was measured at -0.95 dB at 7 GHz and -0.69 dB at 20 GHz for the two respective designs.

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